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AMENDMENT TO THE CLAIMS

1. (Currently amended) A semiconductor device comprising:

a gate insulating film having a multilayer structure including a zirconium oxide film and a high dielectric constant film which is a hafnium oxide film or a hafnium aluminate film and which is formed on formed of an oxide of a metal other than zirconium and substantially directly contacting the zirconium oxide film,

~~wherein the high dielectric constant film is a hafnium oxide film or a hafnium aluminate film a silicon nitride film is formed under the zirconium oxide film.~~

2. (Canceled)

3. (Original) The semiconductor device of claim 1, wherein the high dielectric constant film contains nitrogen.

4. (Currently amended) The semiconductor device of claim 1, wherein ~~the gate insulating film includes a zirconium silicate film formed under the interface between the silicon nitride film and the zirconium oxide film is formed of a zirconium silicate film.~~

5-22. (Canceled)

23. (Currently amended) The semiconductor device of claim [[22]] 1, wherein the silicon nitride film has a thickness of 1 nm or less.

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24. (Previously presented) The semiconductor device of claim 1, further comprising a gate electrode on the gate insulating film.

25. (Previously presented) The semiconductor device of claim 24, wherein the gate electrode is a titanium nitride film.

26. (Previously presented) The semiconductor device of claim 24, wherein the gate electrode has a thickness of not less than 30 nm and not more than 100 nm.

27. (Currently amended) The semiconductor device of claim 24, further comprising [[a]] an insulating sidewall spacer formed to cover the side faces of the gate electrode.

28-30. (Cancelled)

31. (Previously presented) The semiconductor device of claim 24, further comprising a gate electrode on the gate insulating film.

32. (Previously presented) The semiconductor device of claim 31, wherein a gate electrode is a titanium nitride film.

33. (Previously presented) The semiconductor device of claim 31, wherein the gate electrode has a thickness of not less than 30 nm and not more than 100 nm.

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34. (Currently amended) The semiconductor device of claim 31, further comprising [[a]] an insulating sidewall spacer formed to cover the side faces of the gate electrode.

35. (Currently amended) The semiconductor device of claim 1, wherein the high dielectric constant film substantially directly contacts the top surface of the zirconium oxide film.

36. (Cancelled)